

# DATA SHEET

**PMBFJ111;  
PMBFJ112; PMBFJ113**  
N-channel junction FETs

Product specification  
File under Discrete Semiconductors, SC07

April 1995

# N-channel junction FETs

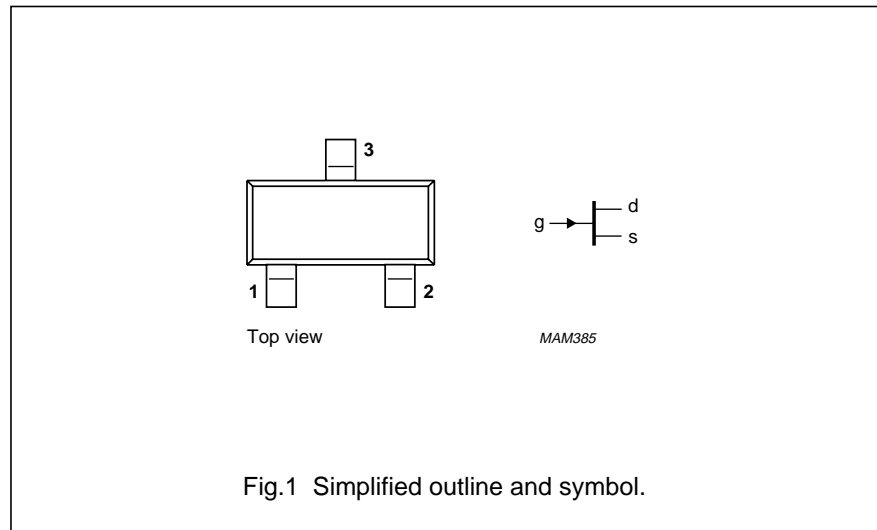
# PMBFJ111; PMBFJ112; PMBFJ113

### FEATURES

- High-speed switching
- Interchangeability of drain and source connections
- Low  $R_{DSon}$  at zero gate voltage ( $< 30 \Omega$  for PMBFJ111).

### DESCRIPTION

Symmetrical N-channel junction FETs in a surface mount SOT23 envelope. Intended for use in applications such as analog switches, choppers, commutators, multiplexers and thin and thick film hybrids.



### PINNING - SOT23

PIN	DESCRIPTION
1	drain
2	source
3	gate

### Note

1. Drain and source are interchangeable.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage		–	$\pm 40$	V
$V_{GSO}$	gate-source voltage		–	–40	V
$V_{GDO}$	drain-drain voltage		–	–40	V
$I_G$	forward gate current (DC)		–	50	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25 \text{ }^\circ\text{C}$ ; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	150	$^\circ\text{C}$
$T_j$	operating junction temperature		–	150	$^\circ\text{C}$

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$$T_j = P(R_{th\ j-t} + R_{th\ t-s} + R_{th\ s-a}) + T_{amb}$$

SYMBOL	PARAMETER	MAX.	UNIT
$R_{th\ j-a}$	from junction to ambient (note 1)	430	K/W
$R_{th\ j-a}$	from junction to ambient (note 2)	500	K/W

**Notes**

1. Mounted on a ceramic substrate, 8 mm × 10 mm × 0.7 mm.
2. Mounted on printed circuit board.

**STATIC CHARACTERISTICS**

$$T_j = 25\text{ }^{\circ}\text{C.}$$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-I_{GSS}$	reverse gate current	$-V_{GS} = 15\text{ V}; V_{DS} = 0$	–	1	nA
$I_{DSS}$	drain current PMBFJ111 PMBFJ112 PMBFJ113	$V_{GS} = 0; V_{DS} = 15\text{ V}$	20 5 2	– – –	mA
$-V_{(BR)GSS}$	gate-source breakdown voltage	$-I_G = 1\text{ }\mu\text{A}; V_{DS} = 0$	40	–	V
$-V_{GS(off)}$	gate-source cut-off voltage PMBFJ111 PMBFJ112 PMBFJ113	$I_D = 1\text{ }\mu\text{A}; V_{DS} = 5\text{ V}$	3 1 0.5	10 5 3	V
$R_{DS(on)}$	drain-source on-resistance PMBFJ111 PMBFJ112 PMBFJ113	$V_{GS} = 0\text{ V}; V_{DS} = 0.1\text{ V}$	– – –	30 50 100	$\Omega$

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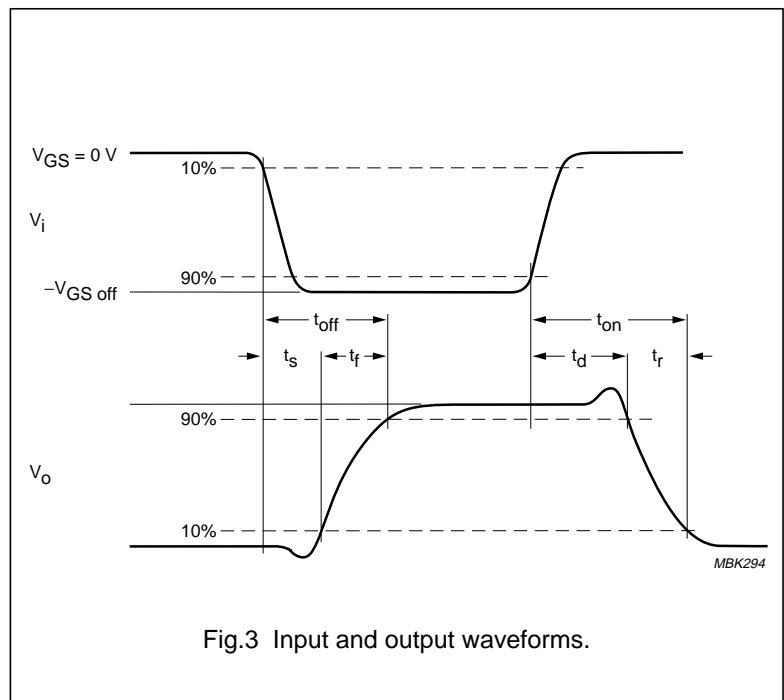
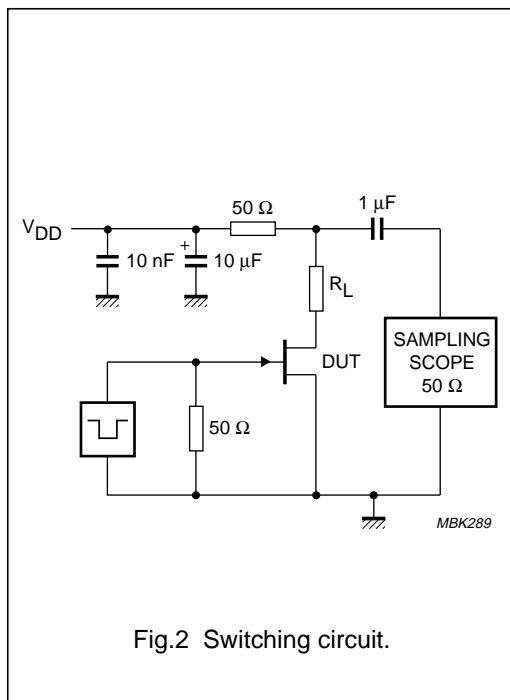
**DYNAMIC CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$ .

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$C_{iss}$	input capacitance	$V_{DS} = 0$ $-V_{GS} = 10\text{ V}$ $f = 1\text{ MHz}$	6	–	pF
		$V_{DS} = 0$ $-V_{GS} = 0$ $f = 1\text{ MHz}$ $T_{amb} = 25\text{ }^\circ\text{C}$	22	28	pF
$C_{rss}$	feedback capacitance	$V_{DS} = 0$ $-V_{GS} = 10\text{ V}$ $f = 1\text{ MHz}$	3	–	pF
<b>Switching times</b> (see Fig.2)					
$t_r$	rise time	note 1	6	–	ns
$t_{on}$	turn-on time	note 1	13	–	ns
$t_f$	fall time	note 1	15	–	ns
$t_{off}$	turn-off time	note 1	35	–	ns

**Notes**

- Test conditions for switching times are as follows:  
 $V_{DD} = 10\text{ V}$ ,  $V_{GS} = 0$  to  $-V_{GS(off)}$  (all types);  
 $-V_{GS(off)} = 12\text{ V}$ ,  $R_L = 750\text{ }\Omega$  (PMBFJ111);  
 $-V_{GS(off)} = 7\text{ V}$ ,  $R_L = 1550\text{ }\Omega$  (PMBFJ112);  
 $-V_{GS(off)} = 5\text{ V}$ ,  $R_L = 3150\text{ }\Omega$  (PMBFJ113).



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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



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<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Short-form specification	The data in this specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

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